

SANYO Semiconductors DATA SHEET



Monolithic Linear IC

LA75520K — IF Signal Processing (VIF+SIF) IC that Supports the PAL Video Standard for TV Sets and VCRs

Overview

The LA75520K is a fully adjustment-free VIF + SIF signal processing IC for TV sets and VTRs that supports the PAL video standard. It supports 38.0MHz, 38.9MHz, and 39.5MHz as the IF frequencies, as well as PAL sound multi-system (M/N, B/G, I and D/K), and contains an on-chip sound carrier trap. The IC employs a 4MHz frequency (which can be switched to 4.43MHz) as the reference frequency of the adjustment free circuit, and controls the VCO, AFT, and sound filter using an external input signal.

Features

- Internal VCO adjustment free circuit eliminating the need for an external VCO coil.
- Internal sound carrier trap enables easy configuration of PAL sound multi-system at low cost.
- Considerably reduces the number of required peripheral parts.
- Use of digital AFT eliminates a problem of AFT tolerance.
- Package: DIP24S (300mil)

Functions

- VIF amplifier
- Adjustment-free VCO and PLL detector circuit
- Digital AFT circuit
- RF AGC
- Buzz canceller

- EOAMP
- Internal sound carrier trap
- First SIF detector circuit
- PLL-FM detector circuit

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Specifications

Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC}		6	V
Allowable power dissipation	Pd max	Ta \leq 70°C, Mounted on a substrate.*	700	mW
Operating temperature	Topr		-20 to +70	°C
Storage temperature	Tstg		-55 to +150	°C

* Mounted on a substrate : 76.1×114.3×1.6mm³, glass epoxy board.

Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage	V _{CC}		5.0	V
Operating supply voltage	V _{CC} op		4.5 to 5.5	V

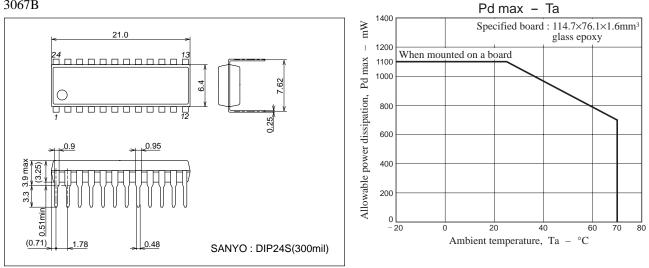
Electrical Characteristics at $Ta = 25^{\circ}C$, $V_{CC} = 5.0V$, fp = 38.9MHz

Parameter	Symbol	Conditions	No.		Ratings		Unit
Falameter	Symbol	Conditions	NO.	min	typ	max	Onit
VIF block							
Circuit current	I ₄		V1	75	85	95	mA
Max RF AGC voltage	V ₁₄ H		V2	4.0	4.5	5.0	V
Min RF AGC voltage	V ₁₄ L		V3	0.0	0.5	1.0	V
Input sensitivity	Vi	Video out 2	V4	26	32	38	dBμV
AGC range	GR		V5	58	63		dB
Max allowable input	V _i max		V6	95	100		dBμV
Quiescent video output voltage	V ₅		V7	2.2	2.5	2.8	V
Sync signal edge voltage	V ₅ tip		V8	0.8	1.0	1.2	V
Video output level	VO		V9	1.0	1.2	1.4	Vp-p
Black noise threshold voltage	VBTH		V10	0.5	0.8	1.1	V
Black noise clamp voltage	VBCL		V11	1.2	1.5	1.8	V
Video S/N	S/N	B/G	V12	46	50		dB
C-S best	IC-S	P/S = 10dB	V13	38	43		dB
Differential gain	DG	$V_{IN} = 80 dB\mu$	V14		3	6.5	%
Differential phase	DP		V15		3	5	deg
Quiescent AFT voltage	V ₁₂	15pin to V _{CC}	V16	2.0	2.5	3.0	V
Max AFT voltage	V ₁₂ H	LOAD 22kΩ/22kΩ	V17	4	4.5	5	V
Min AFT voltage	V ₁₂ L	LOAD 22kΩ/22kΩ	V18	0	0.5	1	V
AFT sensitivity	SF	LOAD 22kΩ/22kΩ	V19	8.5	12.5	16.5	mV/kHz
APC pull-in range (U)	Fpu		V20	2.0	2.4		MHz
APC pull-in range (L)	Fpl		V21		-2.4	-2.0	MHz
VCO control sensitivity	β		V22	3	6	12	kHz/mV
VIF input resistance	Ri	38.9MHz	V23		1.0	1.5	kΩ
VIF input capacity	Ci	38.9MHz	V24		3	6	pF
N trap1 (4.5M)	NT1	wrt 1MHz	V25	-30	-35		dB
N trap2 (4.8M)	NT2	wrt 1MHz	V26	-19	-24		dB
BG trap1 (5.5M)	BT1	wrt 1MHz	V27	-27	-32		dB
BG trap2 (5.85M)	BT2	wrt 1MHz	V28	-20	-25		dB
l trap1 (6.0M)	IT1	wrt 1MHz	V29	-25	-30		dB
l trap2 (6.55M)	IT2	wrt 1MHz	V30	-15	-20		dB
DK trap1 (6.5M)	DT1	wrt 1MHz	V31	-25	-30		dB
Group delay 1 NTSC (3.0M)	NGD1	wrt 1MHz	V32	30	80	145	ns
Group delay 1-1 NTSC (3.5M)	NGD1-1	wrt 1MHz	V33	110	200	290	ns
Group delay 2 BG (4M)	BGD2	wrt 1MHz	V34	50	130	210	ns
Group delay 2-1 BG (4.4M)	BGD2-1	wrt 1MHz	V35	120	200	280	ns
Group delay 3 I (4M)	IGD3	wrt 1MHz	V36	0	80	130	ns

ontinued from preceding page.					Ratings		
Parameter	Symbol	Conditions	No.	min		max	Unit
Group delay 3-1 I (4.4M)	IGD3-1	wrt 1MHz	V37	80	typ 120	max 160	ns
Group delay 4 DK (4M)	DGD4	wrt 1MHz	V37	10	30	50	ns
Group delay 4-1 DK (4.4M)	DGD4-1	wrt 1MHz	V30	30	60	90	ns
Video f characteristics MN1	VFMN1	M/N 1 to 2MHz	V33	-1.0	0.0	1.0	dB
Video f characteristics MN2	VFMN1 VFMN2	M/N 2 to 3MHz	V40 V41	-1.0	0.0	1.0	dB
Video f characteristics MN3	VFMN2 VFMN3	M/N 3.58MHz	V41 V42		-1.5	0.0	dB
				-3.0			
Video f characteristics BG1	VFBG1	B/G 1 to 3MHz	V43	-1.0	0.0	1.5	dB
Video f characteristics BG2	VFBG2	B/G 3 to 4MHz	V44	-1.5	0.0	1.5	dB
Video f characteristics BG3	VFBG3	B/G 4.43MHz	V45	-2.5	-1.0	0.5	dB
Video f characteristics I1	VFI1	I 1 to 3MHz	V46	-1.0	0.0	1.0	dB
Video f characteristics I2	VFI2	I 3 to 4MHz	V47	-1.0	0.0	1.5	dB
Video f characteristics I3	VFI3	I 4.43MHz	V48	-1.5	0.0	1.5	dB
Video f characteristics DK1	VFDK1	D/K 1 to 3MHz	V49	-1.0	0.0	1.0	dB
Video f characteristics DK2	VFDK2	D/K 3 to 4MHz	V50	-1.0	0.0	1.5	dB
Video f characteristics DK3	VFDK3	D/K 4.43MHz	V51	-1.5	0.0	1.5	dB
Group delay 2-2 BG shift (4M)	BGD2-2	wrt 1MHz	V52	50	100	150	ns
Group delay 2-3 BG shift (4.4M)	BGD2-3	wrt 1MHz	V53	110	180	250	ns
1st SIF Block							
SIF carrier output level 1	So1	V _i = 1mV	F1	21	43	86	mVrms
SIF carrier output level 2	So2	V _i = 10mV	F2	21	43	86	mVrms
1st SIF max input	Si max		F3	110	120		dBμV
1st SIF input resistance	Ris	33.4MHz	F4		2	2.4	kΩ
1st SIF input capacity	Cis	33.4MHz	F5		3	6	pF
SIF Block							
Limiting sensitivity (SPLIT)	V _i (lim) (SP)	P = 80dBµ CW	S1	20	25	30	dBµV
Limiting sensitivity (INTER)	V _i (lim) (IN)	P = 80dBµ P/S	S2	29	35	41	dB
FM detection output voltage	V _O (FM)	f = 5.5MHz, Δ F = ±30kHz	S3	390	560	730	mVrms
AM removal ratio	AMR		S4	50	60		dB
Distortion factor	THD		S5		0.3	0.8	%
FM detection output S/N	S/N (FM)	P = 80dBµ CW	S6	55	60		dB
PAL/NT audio voltage gain difference	GD		S7		6		dB
PAL De-emphasis	Pdeem		S8		-3		dB
NT De-emphasis	Ndeem		S9		-3		dB
Control Block	I.	I					
SIF system SW threshold voltage A/B	V7_9th		C1	2.2	2.5	2.8	V
38MHz/38.9MHz threshold voltage	V10th1		C2	0.7	1.0	1.3	V
38.9MHz/39.5MHz threshold voltage	V10th2		C3	3.7	4.0	4.3	V
Inter-carrier system	V13th		C4			0.3	V
AFT mute level/SIF trap shift	V15th1		C5	0.7	1.0	1.3	V
threshold voltage 1							
AFT mute level/SIF trap shift	V15th2		C6	2.2	2.5	2.8	V
threshold voltage 2			_				
AFT mute level/SIF trap shift	V15th3		C7	3.7	4.0	4.3	V
threshold voltage 3 Others			1				
	Reflev	4.0MHz	01	83	90	95	dBµV
						30	UDUV
Ref clock input level Reference frequency SW threshold	R11		02	150	270		kΩ

Package Dimensions

unit : mm (typ) 3067B



System changeover

a. SIF system SW

The SIF system can be changed over by setting A (pin 7) and B (pin 9) to GND and OPEN respectively.

A	В	BG	I	DK	MN	FM DET LEVEL	De-emphasis
GND	GND				0	6dB	75µs
GND	OPEN			0		0dB	50µs
OPEN	GND		0			0dB	50µs
OPEN	OPEN	0				0dB	50µs

Note : Circles mean that the system indicated with a circle is selected

b. IF system SW

The IF frequency becomes 38.9MHz when pin 10 is open. The IF frequency becomes 38.0MHz when pin 10 is set to GND. The IF frequency becomes 39.5MHz when pin 10 is set to V_{CC} .

c. Split/inter carrier SW

Inter-carrier is selected by setting the 1st SIF input (pin 13) to GND.

d. Reference frequency changeover SW

The reference frequency becomes 4.43MHz when pin 11 is OPEN. The reference frequency becomes 4.0MHz when $270k\Omega$ is connected between pin 11 and GND.

e. AFT mute level, trap point shift SW

By changing the pin 15 voltage, the potential and TRAP point at which AFT is muted can be set to either just or shift (about +220kHz).

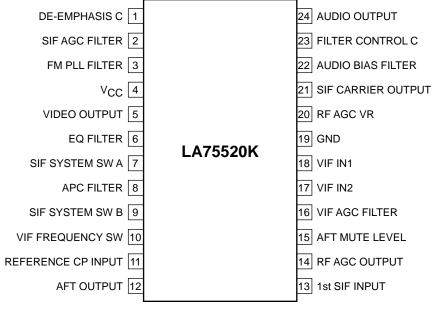
Pin 15 potential	AFT mute potential	TRAP point shift
V _{CC} to 4V	MIDDLE (V _{CC} /2)	Just
4V to 2.5V	MIDDLE (V _{CC} /2)	Shift
2.5V to 1V	HI (V _{CC})	Just
1V to GND	HI (V _{CC})	Shift

* V_{CC}=5V

f. FM detector function not used

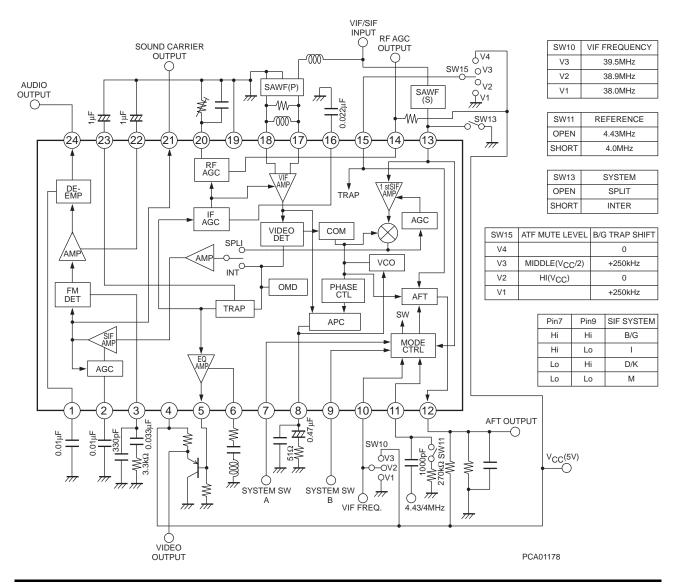
To stop FM detection VCO without using the SIF circuit, short-circuit pin 1 – GND with resistance of $1k\Omega$ or less.

Pin Assignment



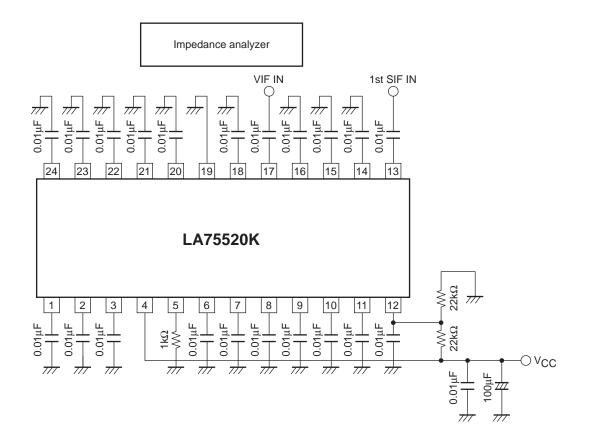
Top View

Block Diagram and Sample Application



LA75520K

Input Impedance Test Circuit (VIF and first SIF input impedance)



Pin Fu	unctions		
Pin No.	Pin name	Function	Equivalent Circuit
1	DE-EMPHASIS C	De-emphasis capacitor connection pin This is used to switch the equivalent resistance ($5k\Omega$ or $7.5k\Omega$) internally in the IC to select the time constant. This switching is linked to the SIF input switch. To disable de-emphasis, disconnect the capacitor. Connection of an external capacitance of 0.01μ F enables switching between 50 and 75 μ s. When the FM detector circuit is not to be used, the FM VCO can be stopped by connecting it to ground with a resistor of $1k\Omega$ or less.	
2	SIF AGC FILTER	AGC filter pin for SIF carrier 0.01µF is recommended for C1.	
3	FM PLL FILTER	PLL filter pin of FM detector This is used to configure an external lag lead filter. Example: Connect 330pF in parallel with the filter on the left (0.033 μ F + 3.3k Ω).	
4 5 6	V _{CC} EQ OUT EQ FILTER	Power supply Equalizer circuit. This circuit is used to correct the video signal frequency characteristics. Notes on equalizer amplifier design • The equalizer amplifier is designed as a voltage follower amplifier with a gain of about 0 dB. When used for frequency characteristics correction, a capacitor, inductor, and resistor must be connected in series between pin 6 and ground. Equalizer amplifier gain AV = $\frac{R1}{Z}$ + 1 R1 is the IC internal resistance, and is 1kΩ. In the application design, simply select Z to correspond to the desired characteristics. However, since the EQ amplifier gain will be maximum at the resonant point defined by Z, care is required to assure that distortion does not occur.	

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	rom preceding page.	Function	Equivalent Circuit
Pin No.	Pin name	Function	Equivalent Circuit
7 9	SIF SYSTEM SW A	SIF system selection switch pins. Combining the settings of these two pins supports four systems. In M/N mode, the audio output level is increased by 6dB. The internal trap is also linked to these switches. The truth-values are as follows. Pin7 Pin9 MODE H H L H D/K	80kt3 1kt3 00kt3 1kt3 00kt3 1kt3 00kt3 1kt3 00kt3 1kt3 00kt3
8	APC FILTER	L M/N PLL APC filter connection pin. The APC count is switched internally in the IC. The VCO is normally controlled by route A. When unlocked and during weak field reception, the VCO is controlled by route B and the loop gain is	
		increased. For this APC filter we recommend a resistor of 51Ω and capacitor of 0.47μ F. The buzz characteristics can be improved by connecting a capacitor of 100pF or so between pins 5 and 8.	
10	VIF FREQUENCY SW	Switch pin for selecting the IF frequency When this pin is open, $1/2V_{CC}$ exists. V_{CC} : 39.5MHz Open : 38.9MHz GND : 38.0MHz	50kΩ 10 50kΩ 11kΩ 50kΩ
11	REFERENCE CP INPUT	Reference signal input pin necessary for adjusting the internal sound carrier trap, AFT, etc. Either 4.0 or 4.43 MHz can be selected. Use the configuration shown in example 1 when using 4.43MHz and configuration shown in example 2 when using 4.0MHz. Since no oscillator can be configured simply by connecting the X'tal resonator to pin 11, input the reference signal from an external source without fail. Example 1 $1000pF - 1000pF - 270k\Omega$ 4.43MHz - 4.0MHz	

	1 91 9	Function	Equivalent Circuit
Pin No. 12	rom preceding page. Pin name AFT OUTPUT	Function AFT output pin. The AFT center voltage is generated by an external bleeder resistor. gain is increased by increasing the resistan external bleeder resistor. For the resistor we recommend a resistan to or greater than 22kΩ. For the filter C1 we recommend a capacita 0.1µF.	The AFT noce of this ce equal ance of R C1
13	1st SIF INPUT	First SIF input pin. A DC cut capacitor musi in the input circuit. (a) If a SAW filter is used : The first SIF sensitivity can be increased to inserting an inductor between the SAW filter IC to neutralize the SAW filter output capa and the IC input capacitance. (b) When used in an intercarrier system : Connect this pin to ground.	by $2k\Omega$ T
14	RF AGC OUTPUT	RF AGC output pin. This output controls the RF AGC. This is the open collector output and a properties of the open collector output and a properties of the time the expectation of the time.	tective
15	AFT MUTE LEVEL	Voltage V _{CC} to 4V V _{CC} /2 4V to 2.5V V _{CC} /2 2.5V to 1V V _{CC}	nlock, etc. rap point Vhen the d are to nput, the ugh the herefore, $\leq 66k\Omega$

Pin No.	rom preceding page. Pin name	Function	Equivalent Circuit
16	IF AGC	IF AGC filter connection pin. The signal peak-detected by the built-in AGC detector is converted to the AGC voltage at pin 16. Additionally, a second AGC filter (a lag-lead filter) used to create the dual time constants is provided internally in the IC. Use a 0.022µF capacitor as the external capacitor (C1), and adjust the value according to the sag, AGC speed, and other characteristics.	$\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
17 18	VIF IN2 VIF IN1	VIF amplifier input pin The input circuit is a balanced circuit, and the input impedance is as follows: $R \approx 1.0 k\Omega$	
19	GND		
20	RF AGC VR	RF AGC volume connection pin This pin sets the tuner RF AGC operating point. Also, the FM output and the video output can both be muted at the same time by connecting this pin to ground.	
21	SIF CARRIER OUT	First SIF output pin This is an emitter-follower output with a 200Ω resistor attached in series.	→ → → → → → → → → → → → → →
22	AUDIO BIAS FILTER	Connection pin for a filter used to hold the FM detector output DC voltage fixed. Normally, a 1μ F electrolytic capacitor should be used. The capacitance (CI) should be increased if the low band (around 50Hz) frequency characteristics need to be improved.	30000 40k0 40k0 40k0 40k0 10 10 10 10 10 10 10 10 10 1

Pin No.	Pin name	Function	Equivalent Circuit
23	FILTER CONTROL C	Internal filter (trap) control pin Connect a capacitor with a capacitance between 0.47 to 1 μ F, depending on the video S/N as well as the levels of the AM and PM noise.	
24	AUDIO OUTPUT	Sound output pin Emitter follower output	

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